

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRIAC

## TLP3061(S), TLP3062(S), TLP3063(S)

OFFICE MACHINE

HOUSEHOLD USE EQUIPMENT

TRIAC DRIVER

SOLID STATE RELAY

Unit in mm

The TOSHIBA TLP3061 (S), TLP3062 (S) and TLP3063 (S) consist of a zero voltage crossing turn-on photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

All parameters are tested to the specification of TLP3061, TLP3062, TLP3063.

- Peak Off-State Voltage : 600V (min)
- Trigger LED Current : 15mA (max) (TLP3061)  
10mA (max) (TLP3062)  
5mA (max) (TLP3063)
- On-State Current : 100mA (max)
- UL Recognized : UL1577, File No. E67349
- Isolation Voltage : 5000V<sub>rms</sub> (min)
- SEMKO Approved : SS EN60065  
SS EN60950
- BSI Approved : BS EN60065  
BS EN60950
- Option (D4) Type  
VDE Approved : DIN VDE0884 / 06.92  
Certificate No. 68329

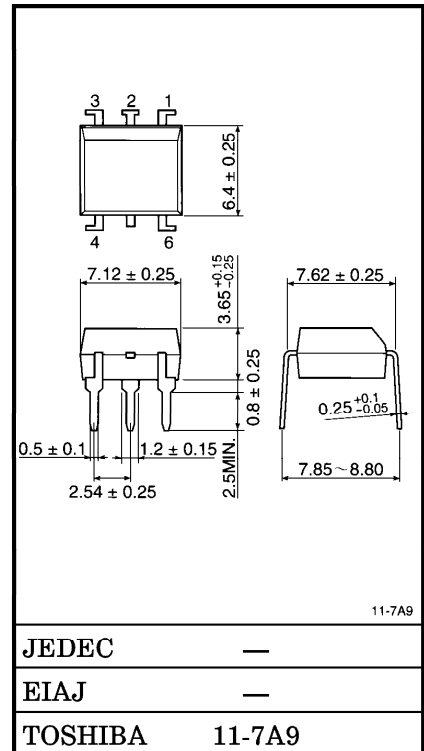
Maximum Operating Insulation Voltage : 890V<sub>PK</sub>

Highest Permissible Over Voltage : 8000V<sub>PK</sub>

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

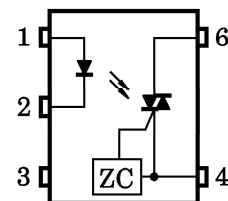
● Device Construction

	7.62mm pich standard type	10.16mm pich (LF2) type
Creepage Distance	7.0mm (min)	8.0mm (min)
Clearance	7.0mm (min)	8.0mm (min)
Insulation Thickness	0.5mm (min)	0.5mm (min)



Weight : 0.39g

PIN CONFIGURATION (Top view)



- 1 : ANODE
- 2 : CATHODE
- 3 : N.C.
- 4 : TERMINAL 1
- 6 : TERMINAL 2

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● TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.

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## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current	$I_F$	50	mA
	Forward Current Derating (Ta ≥ 53°C)	$\Delta I_F / ^\circ\text{C}$	-0.7	mA / °C
	Peak Forward Current (100 $\mu\text{s}$ pulse, 100pps)	$I_{FP}$	1	A
	Power Dissipation	$P_D$	100	mW
	Power Dissipation Derating (Ta ≥ 25°C)	$\Delta P_D / ^\circ\text{C}$	-1.0	mW / °C
	Reverse Voltage	$V_R$	5	V
	Junction Temperature	$T_j$	125	°C
DETECTOR	Off-State Output Terminal Voltage	$V_{DRM}$	600	V
	On-State RMS Current	Ta = 25°C	100	mA
		Ta = 70°C	50	
	On-State Current Derating (Ta ≥ 25°C)	$\Delta I_T / ^\circ\text{C}$	-1.1	mA / °C
	Peak On-State Current (100 $\mu\text{s}$ pulse, 120pps)	$I_{TP}$	2	A
	Peak Nonrepetitive Surge Current (P <sub>w</sub> = 10ms, DC = 10%)	$I_{TSM}$	1.2	A
	Power Dissipation	$P_D$	300	mW
	Power Dissipation Derating (Ta ≥ 25°C)	$\Delta P_D / ^\circ\text{C}$	-4.0	mW / °C
	Junction Temperature	$T_j$	115	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C	
Operating Temperature Range	$T_{opr}$	-40~100	°C	
Lead Soldering Temperature (10s)	$T_{sol}$	260	°C	
Total Package Power Dissipation	$P_T$	330	mW	
Total Package Power Dissipation Derating (Ta ≥ 25°C)	$\Delta P_T / ^\circ\text{C}$	-4.4	mW / °C	
Isolation Voltage (AC, 1min., R.H. ≤ 60%) (Note 1)	$BV_S$	5000	V <sub>rms</sub>	

(Note 1) Device considered a two terminal device : Pins 1, 2 and 3 shorted together and pins 4 and 6 shorted together.

## RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	$V_{AC}$	—	—	240	V <sub>ac</sub>
Forward Current	$I_F^*$	15	20	25	mA
Peak On-State Current	$I_{TP}$	—	—	1	A
Operating Temperature	$T_{opr}$	-25	—	85	°C

\* In the case of TLP3062

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- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
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INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	$V_F$	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	$I_R$	$V_R = 5\text{V}$	—	—	10	$\mu\text{A}$
	Capacitance	$C_T$	$V = 0, f = 1\text{MHz}$	—	10	—	pF
DETECTOR	Peak Off-State Current	$I_{DRM}$	$V_{DRM} = 600\text{V}$	—	10	1000	nA
	Peak On-State Voltage	$V_{TM}$	$I_{TM} = 100\text{mA}$	—	1.7	3.0	V
	Holding Current	$I_H$	—	—	0.6	—	mA
	Critical Rate of Rise of Off-State Voltage	$dv/dt$	$V_{in} = 240\text{Vrms}, T_a = 85^\circ\text{C}$ (Fig.1)	200	500	—	$\text{V}/\mu\text{s}$
	Critical Rate of Rise of Commutating Voltage	$dv/dt(c)$	$V_{in} = 60\text{Vrms}, I_T = 15\text{mA}$ (Fig.1)	—	0.2	—	$\text{V}/\mu\text{s}$

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	TLP3061	$I_{FT}$	$V_T = 6\text{V}$	—	—	15	mA
	TLP3062			—	5	10	
	TLP3063			—	—	5	
Inhibit Voltage	$V_{IH}$	$I_F = \text{Rated } I_{FT}$	—	—	50	V	
Leakage in Inhibited State	$I_{IH}$	$I_F = \text{Rated } I_{FT}$ $V_T = \text{Rated } V_{DRM}$	—	100	300	$\mu\text{A}$	
Capacitance Input to Output	$C_S$	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF	
Isolation Resistance	$R_S$	$V_S = 500\text{V} (\text{R.H.} \leq 60\%)$	$5 \times 10^{10}$	$10^{14}$	—	$\Omega$	
Isolation Voltage	$BV_S$	AC, 1 minute	5000	—	—	$V_{rms}$	
		AC, 1 second, in oil	—	10000	—		
		DC, 1 minute, in oil	—	10000	—	$V_{dc}$	

Fig. 1  $dv/dt$  TEST CIRCUIT

